PUA3112 (PU3112)

Silicon NPN epitaxial planar type

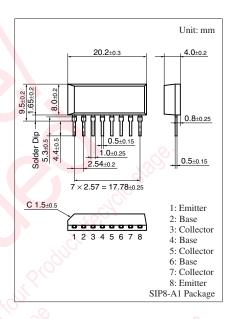
For power amplification/switching Complementary to PUA3212 (PU3212)

■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
- \bullet Low collector-emitter saturation voltage $V_{\text{CE}(\text{sat})}$
- NPN 3 elements

■ Absolute Maximum Ratings $T_C = 25$ °C

| Parameter | Symbol | Rating | Unit | |
|---------------------------------------|------------------|-------------|------|--|
| Collector-base voltage (Emitter open) | V_{CBO} | 130 | V | |
| Collector-emitter voltage (Base open) | V _{CEO} | 80 | V | |
| Emitter-base voltage (Collector open) | V _{EBO} | 7 | V | |
| Collector current | I_{C} | 3 | A | |
| Peak collector current | I_{CP} | 6 | A | |
| Collector power dissipation | P _C | 15 | W | |
| $T_a = 25^{\circ}C$ | | 2.4 | | |
| Junction temperature | T _j | 150 | °CO | |
| Storage temperature | T_{stg} | -55 to +150 | °C | |
| | | | | |

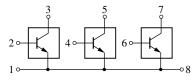


■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

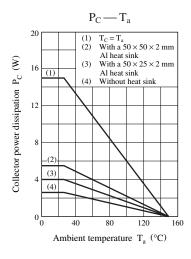
| Parameter | Symbol | Conditions | Min | Тур | Max | Unit |
|--|----------------------|--|-------|------|-----|------|
| Collector-emitter voltage (Base open) | V _{CEO} | $I_C = 10 \text{ mA}, I_B = 0$ | 80 | 0/// | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 100 \text{ V}, I_{E} = 0$ | D. 10 | 5- | 10 | μΑ |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 5 \text{ V}, I_{C} = 0$ | 0,0. | | 50 | μΑ |
| Forward current transfer ratio | h _{FE1} | $V_{CE} = 2 \text{ V}, I_{C} = 0.1 \text{ A}$ | 45 | | | _ |
| | h _{FE2} | $V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}$ | 60 | | 260 | |
| Collector-emitter saturation voltage | V _{CE(sat)} | $I_C = 2 \text{ A}, I_B = 0.1 \text{ A}$ | | | 0.5 | V |
| Base-emitter saturation voltage | V _{BE(sat)} | $I_C = 2 A, I_B = 0.1 A$ | | | 1.5 | V |
| Transition frequency | f_T | $V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 10 \text{ MHz}$ | | 30 | | MHz |
| Turn-on time | t _{on} | $I_{\rm C} = 0.5 \text{ A}$ | | 0.5 | | μs |
| Storage time | t _{stg} | $I_{B1} = 50 \text{ mA}, I_{B2} = -50 \text{ mA}$ | | 2.5 | | μs |
| Fall time | t _f | $V_{CC} = 50 \text{ V}$ | | 0.15 | | μs |

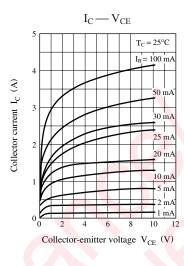
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

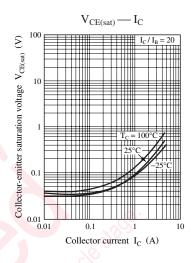
■ Internal Connection

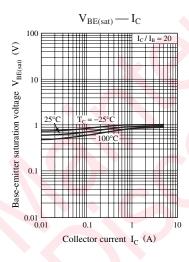


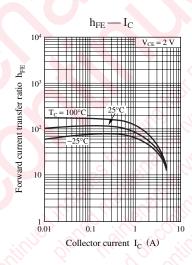
Note) The part number in the parenthesis shows conventional part number.

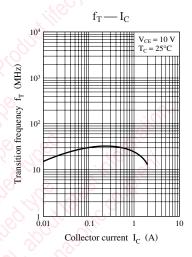


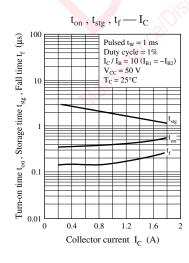


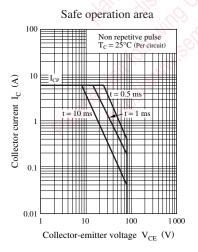












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